

N-channel TrenchMOS standard level FET 19 June 2015

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia General Purpose Automotive (GPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources

3. Applications

- 12 V and 24 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C; <u>Fig. 2; Fig. 3</u>	-	-	7	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	-	8	W
Static charact	eristics	·				
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 9; Fig. 10	-	68	80	mΩ
Avalanche rug	jgedness	-				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 7 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	53	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G
4	D	drain	L1 L2 L3 SC-73 (SOT223)	mbb076 S

6. Ordering information

Table 3. Ordering in	formation						
Type number	Package						
	Name	Description	Version				
BUK7880-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				
BUK7880-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7880-55A	788055A
BUK7880-55A/CU	788055

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	55	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	55	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	8	W
I _D	drain current	T _{sp} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	5	А
		T _{sp} = 25 °C; V _{GS} = 10 V; <u>Fig. 2; Fig. 3</u>	-	7	А
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 3	-	30	А

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
Source-drain	diode					
I _S	source current	T _{sp} = 25 °C		-	7	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$		-	30	А
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 7 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} &= 10 \text{ V}; \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$		-	53	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 4	[1][2][3]	4 <u>1</u>	-	J

[1]

Maximum value not quoted. Repetitive rating defined in avalanche rating figure. Single-pulse avalanche rating limited by maximum junction temperature of 150 °C. [2]

[3] Repetitive avalanche rating limited by an average junction temperature of 150 °C

Refer to application note AN10273 for further information. [4]

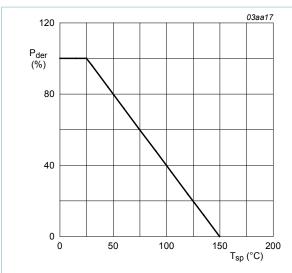


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

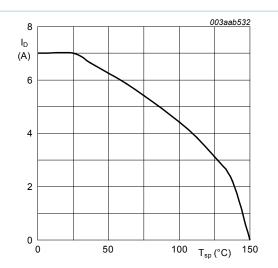
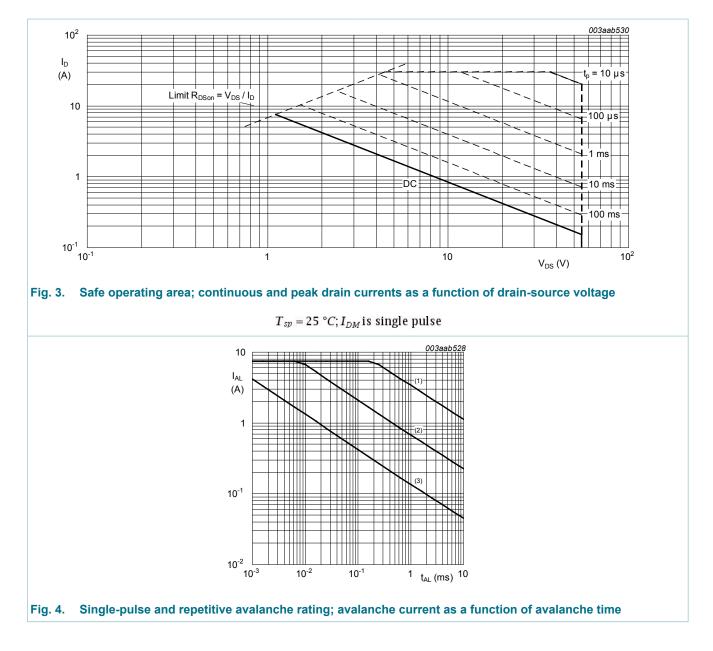


Fig. 2. Continuous drain current as a function of solder point temperature

 $V_{GS} \ge 10 V$

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Thermal characteristics 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	120	-	K/W

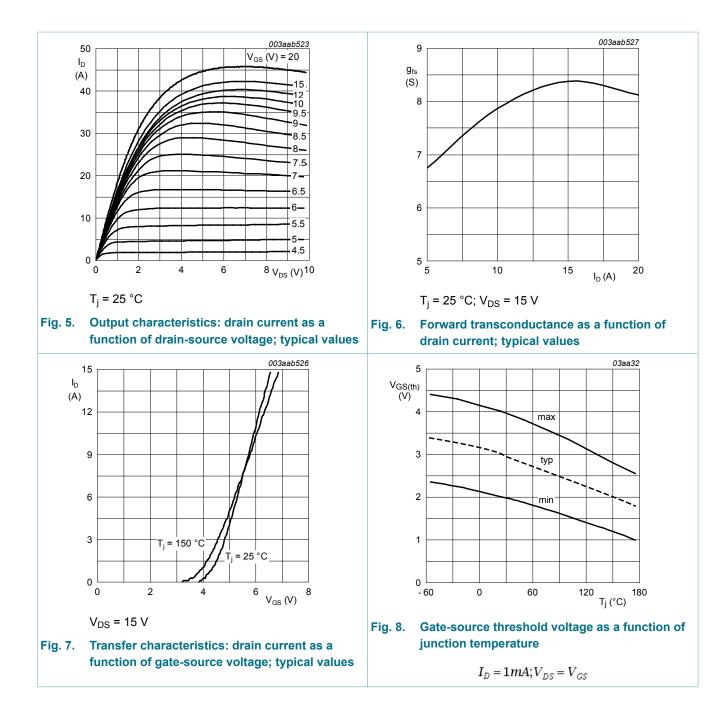
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				_
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; <u>Fig. 8</u>	2	3	4	V
V _{GSth} gate-source voltage	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 8	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; Fig. 8	1.2	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	DSon drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 150 °C; Fig. 9; Fig. 10	-	-	148	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 9; Fig. 10	-	68	80	mΩ
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μA
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·				
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 44 V; V _{GS} = 10 V;	-	12	-	nC
Q _{GS}	gate-source charge	Fig. 11	-	2.5	-	nC
Q _{GD}	gate-drain charge		-	5	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	374	500	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 12</u>	-	92	110	pF
C _{rss}	reverse transfer capacitance		-	62	85	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	52	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	9	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 13</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs;	-	33	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V	-	31	-	nC

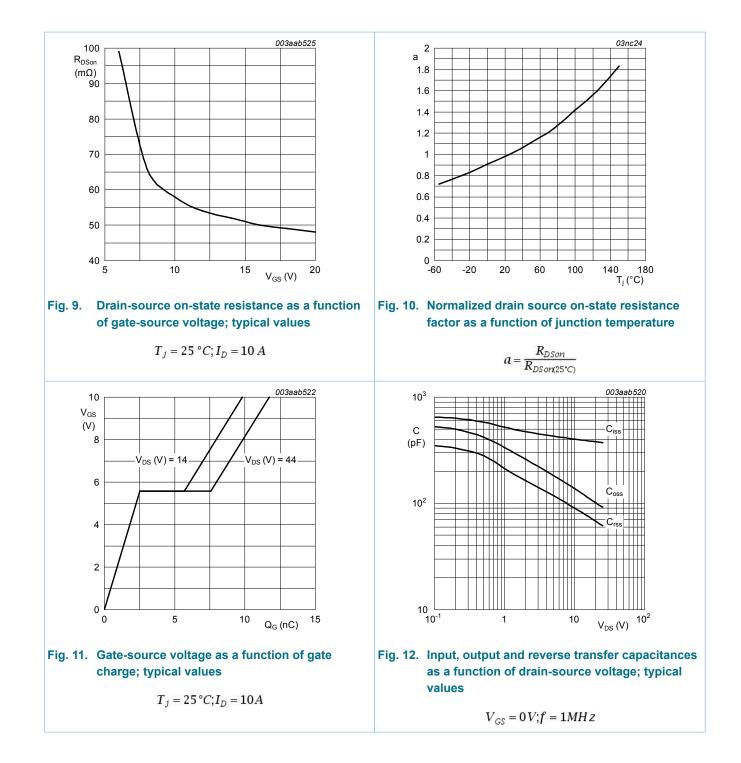
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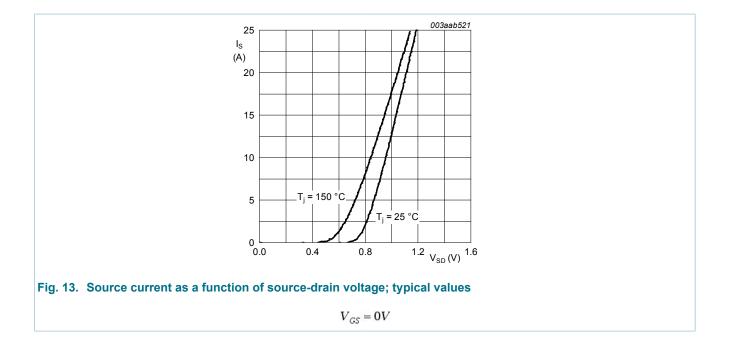
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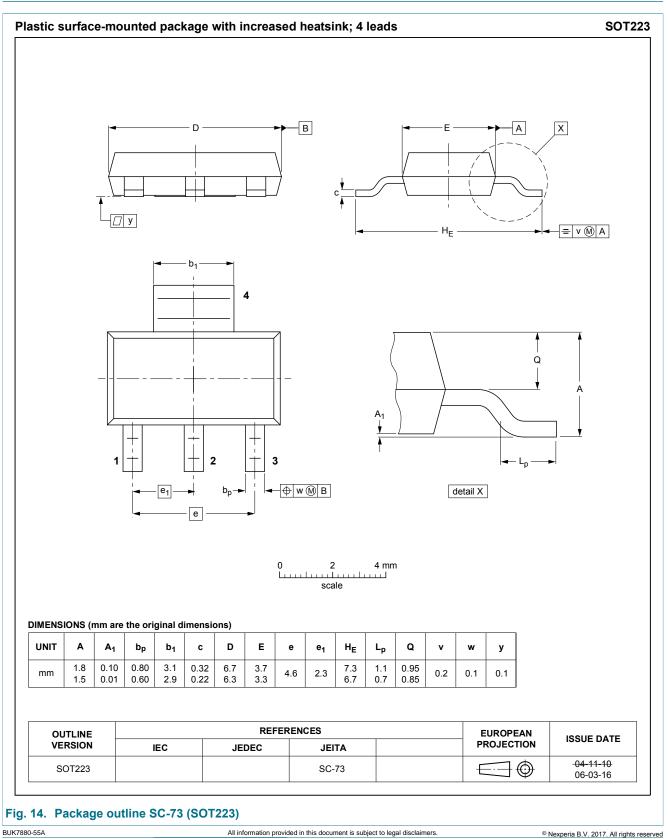
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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